NSN 5961-01-381-8867

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Inclosure Material:

Metal

Overall Length:

Between 0.790 inches and 0.800 inches

Overall Height:

Between 0.249 inches and 0.260 inches

Overall Width:

Between 0.535 inches and 0.545 inches

Mounting Facility Quantity:

1

Internal Configuration:

Field effect

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-254

Mounting Method:

Terminal and unthreaded hole

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

100.0 breakdown voltage, drain-to-source, with all other terminals short-circuited to source and 20.0 gate to source voltage

Current Rating Per Characteristic:

22.00 amperes drain current and 88.00 amperes off-state current, peak

Power Rating Per Characteristic:

125.0 watts total device dissipation

Maximum Operating Tempurature Per Measurement Point:

150.0 degrees celsius junction

Special Test Features:

Environmental stress screening

Test Data Document:

08748-tr162 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) and 08748-tr169 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing.

Terminal Type And Quantity:

3 uninsulated wire lead

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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